

TSM85N08

75V N-Channel Power MOSFET

Pb RoHS COMPLIANCE

TO-220



Pin Definition:

- 1. Gate
- 2. Drain
- Drain
 Source

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
75	8 @ V _{GS} =10V	80

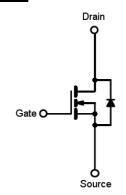
Features

- Advanced Trench Technology
- Low R_{DS(ON)} 8mΩ (Max.)
- Low gate charge typical @ 91.5nC (Typ.)
- Low Crss typical @ 203pF (Typ.)

Ordering Information

Part No.	Package	Packing
TSM80N08CZ C0	TO-220	50pcs / Tube

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	75	V	
Gate-Source Voltage		V_{GS}	±25	V	
	T _C =25℃		80	^	
	T _C =70℃		60		
Continuous Drain Current	T _A =25℃	I _D	12	Α	
	T _A =70℃		9		
Drain Current-Pulsed Note 1		I _{DM}	320	Α	
Avalanche Current, L=0.3mH		I _{AS} , I _{AR}	58	А	
Avalanche Energy, L=0.3mH		E _{AS} , E _{AR}	400	mJ	
	T _C =25℃		113.6		
Maximum Dawer Dissipation	T _C =70℃	P_{D}	72.7	W	
Maximum Power Dissipation	T _A =25℃	P _D	2		
	T _A =70℃		1.3		
Storage Temperature Range		T _{STG}	-55 to +150	C	
Operating Junction Temperature Range		T _J	-55 to +150	C	

^{*} Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R\Theta_{JC}$	1.1	°C/W
Thermal Resistance - Junction to Ambient	$R\Theta_{JA}$	62.5	°C/W

Notes: Surface mounted on FR4 board t ≤ 10sec



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	75			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 40A$	R _{DS(ON)}		7	8	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	V _{GS(TH)}	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge	N/ 00N/ 1 40A	Q_g		91.5		
Gate-Source Charge	$V_{DS} = 30V, I_D = 40A,$ $V_{GS} = 10V$	Q_{gs}		34		nC
Gate-Drain Charge		Q_{gd}		19.9		
Input Capacitance	.,	C _{iss}		3905		
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$	C _{oss}		371		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		203		
Switching						
Turn-On Delay Time		t _{d(on)}		21.5		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 30V,$	t _r		11		C
Turn-Off Delay Time	$R_G = 3.3\Omega$	t _{d(off)}		73		nS
Turn-Off Fall Time		t _f		66		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =20A	V _{SD}	-	0.8	1.3	V
Reverse Recovery Time	I _S = 40A, T _J =25 °C	t _{fr}		36		nS
Reverse Recovery Charge	dl/dt = 100A/us	Q _{fr}		45		nC

Notes:

^{1.} Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

^{2.} $R\theta_{JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R\theta_{JC}$ is guaranteed by design while $R\theta_{CA}$ is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air

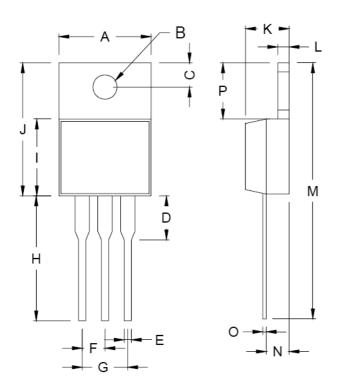


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TO-220 Mechanical Drawing



TO-220 DIMENSION					
DIM	MILLIMETERS		INCHES		
ווועו	MIN	MAX	MIN	MAX	
Α	10.000	10.500	0.394	0.413	
В	3.740	3.910	0.147	0.154	
С	2.440	2.940	0.096	0.116	
D	•	6.350	-	0.250	
Е	0.381	1.106	0.015	0.040	
F	2.345	2.715	0.092	0.058	
G	4.690	5.430	0.092	0.107	
Н	12.700	14.732	0.500	0.581	
J	14.224	16.510	0.560	0.650	
K	3.556	4.826	0.140	0.190	
L	0.508	1.397	0.020	0.055	
М	27.700	29.620	1.060	1.230	
Ν	2.032	2.921	0.080	0.115	
0	0.255	0.610	0.010	0.024	
Р	5.842	6.858	0.230	0.270	



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